IGBT Driver QP12W08S-37A

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Built-in isolated DC-DC power supply; Single power

Built-in fault circuit with a pin for fault feedback Drive signal ignored during blocking time, fault

Adjustable controlled time of fault detection circuit





CE

Patent protection RoHS

Matched IGBT

- 600V series IGBT (current \leq 600A)
- 1,200V series IGBT (current \leq 400A)
- 1,700V series IGBT (current \leq 200A)

Applications

- Universal inverter
- AC servo drive system
- Uninterruptible Power Supply (UPS)
- Electric welding machine

QP12W08S-37A is an integrated hybrid IGBT driver designed with a built-in isolation DC-DC converter. This device is a fully isolated gate drive circuit consisting of an optimally isolated gate drive amplifier and an isolated DC-DC converter. The gate driver provides a fault protection function based on desaturation detection and fault output.

FEATURES

supply drive topology

SIP package

EN62368 approval

High isolation voltage of 3750VAC Input signal frequency up to 20kHz

circuit reset after blocking time end

Adjustable protective soft cut-off time

Selection Guide								
	Input Voltage				Maximum			
Certification	ertification Part No. Input Voltage (VDC)	Output High-level Voltage V _{OH} (VDC)	Output Low-level Voltage V _{OL} (VDC)	Max. Driving Current (A)	capacitive load (uF)			
CE	QP12W08S-37A	12	15	-9	±8	2200		

Maximum ratings					
Item	Symbol	Testing Conditions	Value	Unit	
Power Supply Input Voltage	V_D	DC	13	V	
Input Impulse High-level Current	I _{IH}	Between PIN3 and PIN4	25	mA	
Output Voltage	Vo	Output High-level Voltage	VCC	V	
Driver Output Back Current	Igon	Pulse Width 2us	+8	A	
Driver Output Peak Current	Igoff	Frequency f=20kHz	-8		
Fault Output Current	I fo		20	mA	
Max. Input Voltage to Fault Detect Pin	V_{R1}	Applied PIN13	50	V	

Input Specifications							
Item	Symbol	Testing Conditions	Min.	Typ.	Max.	Unit	
Power Supply	V _D		11.6	12	12.4	V	
Maximum incoming current	I _{In}			180	290	mA	
High-level Input Current	I _{IH}		10	16	20	mA	

Output Specifications						
Item	Symbol	Testing Conditions	Min.	Тур.	Max.	Unit
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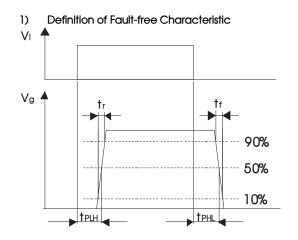
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Isolated Power Supply Voltage		V _{CC}	V _D =12V	14.5		18	
		V_{EE}	V _D =12V	-7		-10	V
	High-level Voltage	V _{OH}	10k Ω Connected Between PIN9-11	13.5	15.0	17.0	v
	Low-level Voltage	V _{OL}	10k Ω Connected Between PIN9-11	-6	-9	-10	
Drive Output	Rise Time	t _r	I⊩=10mA		0.3	1	
	Fall Time	t_f	I _⊩ =10mA		0.3	1	μS

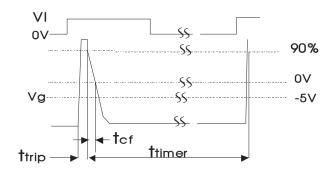
General Spe	cifications							
Item		Symbol	Testing Conditions	Min.	Тур.	Max.	Unit	
Operating Frequency		f		0		20	kHz	
Input ImpulseRise Delay Timeand Drive OutputFall Delay Time		t _{PLH}	I _{IH} =10mA		0.5	1		
		t _{PHL}	I _{IH} =10mA		1	1.3		
Controlled Time of	Detect Fault Circuit	t _{trip}	During the protection operation,the voltage at pin13 \geq 15, pin16 is left floating		1.6		μS	
Fault Soft Turn-off Time		t _{cf}	During the protection operation,the voltage at pin13 \geq 15, pin14 is left floating		4.5			
Fault Reset Time		t _{timer}	Time from start to end of protection signal	1	1.4	2	mS	
Fault Threshold Voltage		V_{ocp}	V _D =12V		9.5		V	
SC Detect Voltage		V _{SC}	Collector Voltage of Module	15				
Fault Output Curre	nt	I_{FO}	PIN15 Input Current, R=4.7k Ω		5		mA	
Gate Resistant		R _g		2			Ω	
Insulation Test		V _{iso}	Sine Wave 50Hz/60Hz, 1min, leakage current <1mA			3750	VAC	
Operating Tempera	ature	T_{op}		-40		70	°C	
Storage Temperature		T_{st}		-50		125	C	
Weight		W			6.0		g	
Safety Standard				EN62368				
Safety Certification				EN62368				
Safety Class				CLASS III				

Design Reference

1. Description of Characteristic



2) Definition of Fault Characteristic

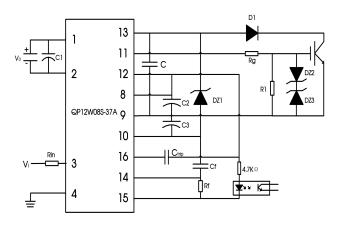




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2. Typical application



VD	12V
VI	5∨±5%
C1	100µF/35V(Low impedance)
C2	100µF/35V(Low impedance)
C3	100µF/35V(Low impedance)
Ctrip	set as required (optional)
Cf	set as required (optional)
Rf	set as required (optional)
Rg	5Ω
RI	10kΩ 0.25W
DZ1	TVS(30V,0.5W)
DZ2, DZ3	TVS(18V,1W)
D1	fast recovery diode (trr≤0.2µs)

1. If the input impulse voltage is too high, the current-limiting resistance can be adjusted to meet the requirements of the input impulse current. A high-speed opto-coupler LED with a 150 $\ensuremath{\Omega}$ series resistance is connected in between the signal input terminals and the current-limiting resistance can be calculated according to the following formula:

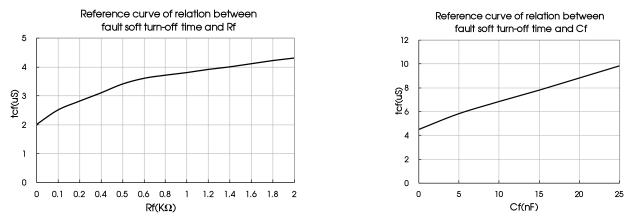
$$R_{in} = \frac{V_I - 1.7V}{I_{III}} - 150\Omega$$

2. For harsh applications in environments with long wires, we recommend adding an additional capacitor C at a distance between pin 9 and pin13 from the unit as appropriate.

(1) Fault soft turn-off time adjustment:

When a short-circuit or an over-current condition occurs, the driver protection circuit activates and slowly turns off the IGBT. The default turn-off time is 4.5µS, and this turn-off time can be adjusted by connecting an external resistor Rf to reduce the time, or capacitor Cf to increase the time. The adjustment range is 2.5µS to 10µS. The values for protective turn-off time adjustment in the table below are for reference only and must be verified to suite the actual application.

Reference values for Fault soft turn-off time adjustment								
R _f (kΩ)	t _{cf} (µS)	C _f (nF)	t _{cf} (µS)					
_	4.5	—	4.5					
1.5	4.0	1	4.9					
0.5	3.5	3.3	5.3					
0.3	3.0	10	6.5					
0.11	2.5	22	9.3					



(2) Controlled fault detection time adjustment:

When a short circuit or an over current condition occurs, the time from the moment the driver detects a short circuit or an over current condition to when the gate potential drops to 90% of the normal amplitude is called "Controlled Time of Fault Detection". The driver sets the default minimum controlled time for the fault detection circuit and the user can increase this time, by connecting an external Ctrip capacitance. The maximum time that can be adjusted is 3.5µS. The values for adjustment controlled short circuit time detection in the table below are for reference only and must be verified to suite the actual application



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 Reference values for Controlled fault detection time adjustment

 Ctrip (nF)
 ttrip (µS)

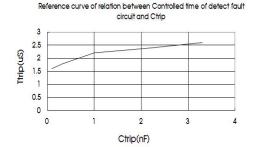
 - 1.6

 0.10
 1.8

 0.33
 2.0

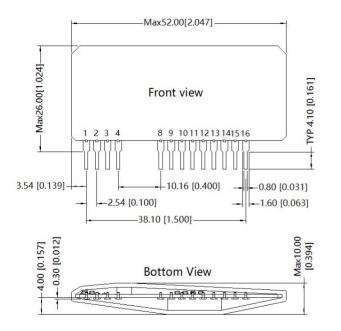
 2.20
 2.4

 3.30
 2.8



3. For additional information please refer to IGBT Driver application notes on www.mornsun-power.com

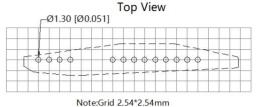
Dimensions and Recommended Layout



Note:

Unit: mm[inch] Pin section tolerances: $\pm 0.10[\pm 0.004]$ General tolerances: $\pm 0.50[\pm 0.020]$

THIRD ANGLE PROJECTION



	Pin-Out		
Pin	Function	Pin	Function
1	Power supply (+)	11	Drive output
2	Power supply (-)	12	Collector of internal power tube
3	Drive signal input(+)	13	Detect of short circuit
4	Drive signal input(-)	14	Adjustment of Soft turn-off time
8	DC/DC converter output (+)	15	Fault signal output
9 DC/DC converter output (COM)		16	Adjustment of short-circuit
10	DC/DC converter output (-)	10	detection time delay

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Notes:

- 1. For additional information on Product Packaging please refer to www.mornsun-power.com. The Packaging bag number: 58230001;
- 2. The maximum capacitive load offered were tested at nominal input voltage and full load;
- 3. The built-in isolated DC-DC power supply is for internal driver use only and cannot be used for external connections.
- 4. The driver must be wired as short as possible to the IGBT module's gate and emitter terminals (1m max.);
- 5. Twisted pair is recommended for the connection of the driver to the gate and emitter of the IGBT;
- 6. In order to reduce the high peak voltage generated at the collector of the IGBT turn-off, it is recommended to increase the gate resistance appropriately;
- 7. The additional capacitor or resistor should be placed as close as possible to the driver terminals. Do not exceed the recommended maximum values;
- 8. Select electrolytic capacitors for C2 and C3 with a low ESR and placed them as close as possible to the driver terminals;
- 9. Select a fast recovery diode D1 (connected to pin13) with a peak reverse voltage that is higher than the peak value of the IGBT collector voltage;
- 10. The 30V Zener diode DZ1 is connected between pin13 and pin10, protecting the driver from the reverse recovery characteristic of the diode D1 which could generate an excessive voltage on pin13;
- 11. 4.7k Ω resistance can be connected between pin13 and pin 9 if fault detection no required.(D1 and DZ1 is not required in this circuit).
- 12. Unless otherwise specified, parameters in this datasheet were measured under the conditions of Ta=25°C, humidity<75%RH with nominal input voltage and rated output load, and measured when Rg=5 Ω;
- 13. All index testing methods in this datasheet are based on company corporate standards;
- 14. The above are the performance indicators of the product models listed in this datasheet. Some indicators of non-standard models will exceed the above requirements. For details, please contact our technical staff;
- 15. We can provide product customization service, please contact our technicians directly for specific information;
- 16. Products are related to laws and regulations: see "Features" ;
- 17. Our products shall be classified according to ISO14001 and related environmental laws and regulations, and shall be handled by qualified units.

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